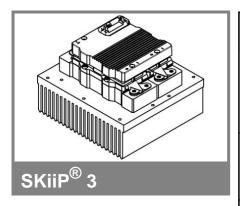
### SKiiP 1013GB172-2DL



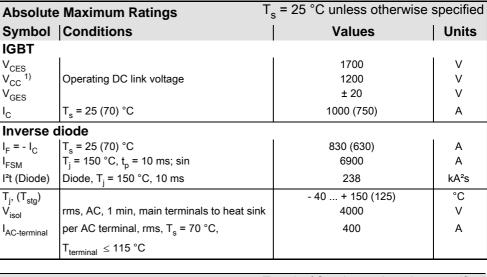
## 2-pack-integrated intelligent Power System

#### Power Section SKiiP 1013GB172-2DL

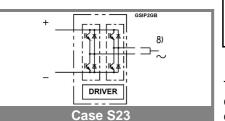
Data

#### **Power section features**

- SKiiP technology inside
- Trench IGBTs
- CAL diode technology
- · Integrated current sensor
- · Integrated temperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP<sup>®</sup> 3 System)
- IEC 60068-1 (climate) 40/125/56
- UL recognized file no. E63532
- with assembly of suitable MKP capacitor per terminal
- 8) AC connection busbars must be connected by the user; copper busbars available on request



Characteristics		$T_s$ = 25 °C unless otherwise specified						
Symbol	Conditions	min.	typ.	max.	Units			
IGBT								
V <sub>CEsat</sub>	$I_C$ = 600 A, $T_j$ = 25 (125) °C; measured at terminal		1,9 (2,2)	2,4	V			
$V_{CEO}$	T <sub>i</sub> = 25 (125) °C; at terminal		1 (0,9)	1,2 (1,1)	V			
r <sub>CE</sub>	T <sub>i</sub> = 25 (125) °C; at terminal		1,5 (2,1)	1,9 (2,5)	mΩ			
I <sub>CES</sub>	$V'_{GE} = 0 \text{ V, } V_{CE} = V_{CES},$ $T_i = 25 (125) \text{ °C}$		2,4 (144)		mA			
E <sub>on</sub> + E <sub>off</sub>	$I_C^3 = 600 \text{ A}, V_{CC} = 900 \text{ V}$		390		mJ			
	T <sub>j</sub> = 125 °C, V <sub>CC</sub> = 1200 V		575		mJ			
R <sub>CC+EE</sub>	terminal chip, T <sub>i</sub> = 25 °C		0,25		mΩ			
L <sub>CE</sub>	top, bottom		6		nH			
C <sub>CHC</sub>	per phase, AC-side		3,4		nF			
Inverse o	liode							
$V_F = V_{EC}$	$I_F = 600 \text{ A}, T_j = 25 \text{ (125) }^{\circ}\text{C}$ measured at terminal		2 (1,8)	2,15	V			
$V_{TO}$	T <sub>i</sub> = 25 (125) °C		1,1 (0,8)	1,2 (0,9)	V			
r <sub>T</sub>	T <sub>i</sub> = 25 (125) °C		1,5 (1,7)		mΩ			
E <sub>rr</sub>	I <sub>C</sub> = 600 A, V <sub>CC</sub> = 900 V		72		mJ			
	T <sub>j</sub> = 125 °C, V <sub>CC</sub> = 1200 V		86		mJ			
Mechanic	cal data							
$M_{dc}$	DC terminals, SI Units	6		8	Nm			
$M_{ac}$	AC terminals, SI Units	13		15	Nm			
W	SKiiP® 3 System w/o heat sink		1,7		kg			
w	heat sink		5,4		kg			
Thermal characteristics (PX 16 heat sink with fan SKF 16B-230-1); "s" reference to heat sink; "r" reference to built-in temperature sensor (acc. IEC 60747-15)								
	<i>•</i>	ı						
th(i-s)I	per IGBT			0,03	K/W			
$R_{th(j-s)I}$ $R_{th(j-s)D}$	per IGBT per diode			0,03 0,058	K/W K/W			
R <sub>th(j-s)D</sub>			tau	0,058				



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0

36

2,3

0,37

50

160

0,06

5

53

0,01

0,25

0,04

0,4

16,4

24

20,3

3,8

24

7,1

9,8

10

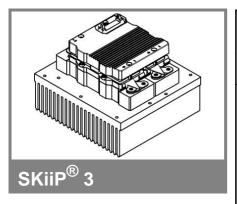
4,3

 $Z_{th(i-r)I}$ 

 $\boldsymbol{Z}_{th(j-r)D}$ 

 $Z_{th(r-a)}$ 

### SKiiP 1013GB172-2DL



# 2-pack-integrated intelligent Power System

2-pack integrated gate driver SKiiP 1013GB172-2DL

Data

#### **Gate driver features**

- CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and

DC-bus voltage (option)

- Short circuit protection
- Over current protection
- Over voltage protection (option)
- Power supply protection against under voltage
- Interlock of top/bottom switch
- Isolation by transformers
- Fibre optic interface (option for GB-types only)
- IEC 60068-1 (climate) 40/85/56
- UL recognized file no. 242581

Absolute	Maximum Ratings T	T <sub>a</sub> = 25 °C unless otherwise specified		
Symbol	Conditions	Values	Units	
$V_{S2}$	unstabilized 24 V power supply	30	V	
$V_{i}$	input signal voltage (high)	15 + 0,3	V	
dv/dt	secondary to primary side	75	kV/μs	
$V_{isollO}$	input / output (AC, rms, )	4000	V	
V <sub>isoIPD</sub>	partial discharge extinction voltage, rms, Q <sub>PD</sub> pC;	1500	V	
V <sub>isol12</sub>	output 1 / output 2 (AC, rms, )	1500	V	
f <sub>sw</sub>	switching frequency	14	kHz	
f <sub>out</sub>	output frequency for I <sub>peak(1)</sub> =I <sub>C</sub>	14	kHz	
$T_{op} (T_{stg})$	operating / storage temperature	- 40 <b>+</b> 85	°C	

Characte	ristics T	<sub>a</sub> = 25 °C unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
$V_{S2}$	supply voltage non stabilized	13	24	30	V
I <sub>S2</sub>	V <sub>S2</sub> = 24 V	320+23*f/kHz+0,00022*(I <sub>AC</sub> /A) <sup>2</sup>			mA
$V_{iT+}$	input threshold voltage (High)			12,3	V
$V_{iT-}$	input threshold voltage (Low)	4,6			V
R <sub>IN</sub>	input resistance		10		kΩ
C <sub>IN</sub>	input capacitance		1		nF
t <sub>d(on)IO</sub>	input-output turn-on propagation time		1,3		μs
t <sub>d(off)IO</sub>	input-output turn-off propagation time		1,3		μs
t <sub>pERRRESET</sub>	error memory reset time		9		μs
$t_{TD}$	top / bottom switch interlock time		3,3		μs
I <sub>analogOUT</sub>	max. 5mA; 8 V corresponds to 15 V supply voltage for external components		1000		Α
I <sub>s1out</sub>	max. load current			50	mA
I <sub>TRIPSC</sub>	over current trip level (I <sub>analoa</sub> OUT = 10 V)		1250		Α
$T_{tp}$	over temperature protection	110		120	°C
UDCTRIP	U <sub>DC</sub> -protection ( U <sub>analog OUT</sub> = 9 V);		not implemented	d	V
	(option for GB types)				

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